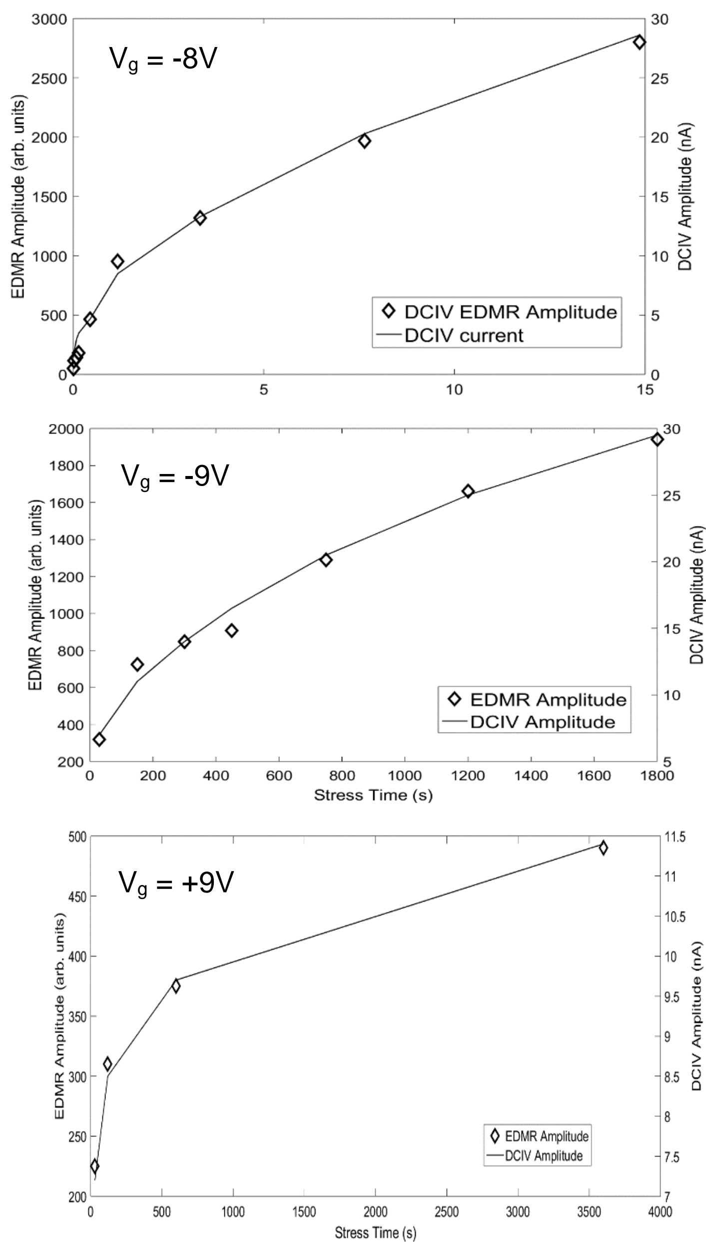

Figure 1. Integrated SDR EDMR amplitude and dc-IV interface recombination current vs. stress time for several different gate stressing conditions.

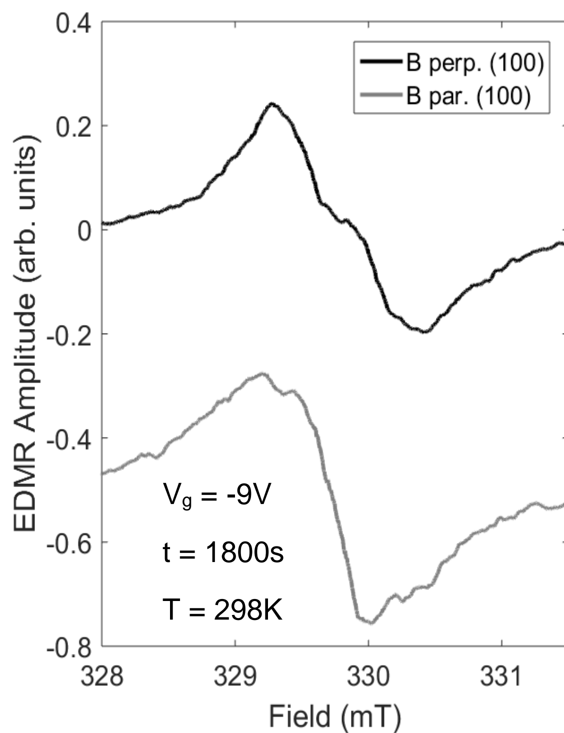

Figure 2. Low-modulation EDMR traces taken at two different magnetic field orientations used to identify Si/SiO_2 interface defects.

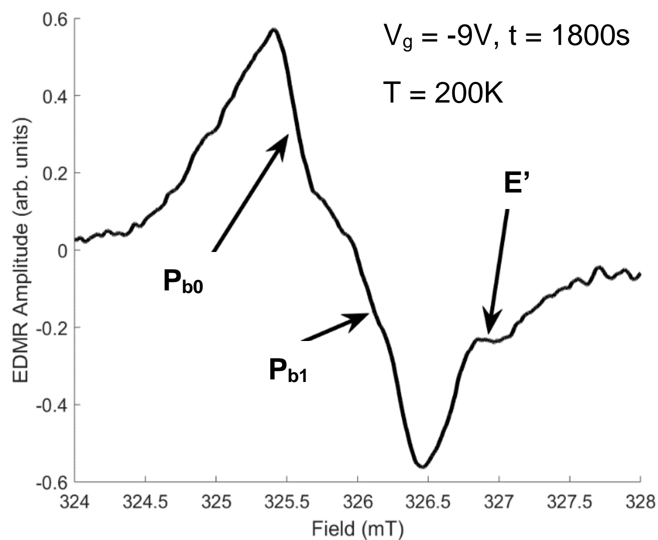

Figure 3. Low-modulation EDMR trace taken at 200K. An additional feature is seen which we attribute to oxide E' centers.

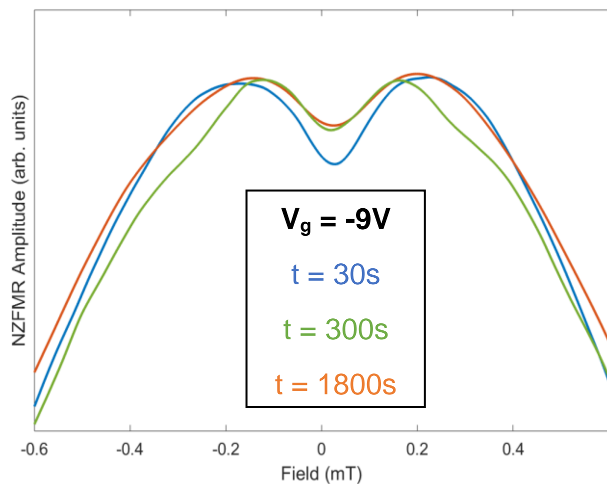

Figure 4. Integrated SDR NZFMR responses after different gate stressing times. Subtle differences in NZFMR lineshape are observed.